

63. (New) The method claim 62, wherein selecting one or more current carrying sections of a substrate is at least partly done with photoresist processing.

64. (New) The method claim 63, wherein the photoresist processing includes at least negative photoresist processing.

65. (New) The method claim 63, wherein the photoresist processing includes at least positive photoresist processing.

66. (New) The method claim 62, wherein selecting one or more current carrying sections of a substrate is at least partly done with silk screening.

67. (New) The method claim 62, wherein selecting one or more current carrying sections of a substrate is at least partly done with patterning.

68. (New) The method claim 62, wherein rendering at least part of the voltage switchable dielectric material conductive includes applying one or more voltages having one or more magnitudes exceeding one or more characteristic voltages of the voltage switchable dielectric material.

69. (New) The method claim 62, wherein electrochemically forming includes electroplating.

70. (New) The method claim 62, wherein electrochemically forming includes plasma deposition.

71. (New) The method claim 62, wherein electrochemically forming includes vapor deposition.

72. (New) The method claim 62, wherein electrochemically forming includes one or more electrostatic processes.

73. (New) The method claim 62, wherein electrochemically forming includes one or more electrolytic processes.

74. (New) The method claim 62, wherein the one or more substrates includes one or more printed circuit boards.

75. (New) The method claim 62, wherein the one or more substrates includes one or more printed wiring boards.

76. (New) The method claim 62, wherein the one or more substrates includes one or more semiconductor wafers.

77. (New) The method claim 62, wherein the one or more substrates includes one or more flex circuit boards.

78. (New) The method claim 62, wherein the one or more substrates includes one or more backplanes.

79. (New) The method claim 62, wherein the one or more substrates includes one or more integrated circuit devices.

80. (New) The method claim 62, wherein the one or more substrates includes one or more semiconductor probe cards.

81. (New) The method claim 62, wherein the one or more substrates includes one or more semiconductor substrates.

82. (New) The method claim 62, wherein the voltage switchable dielectric material includes one or more polymer binders, one or more cross linking agents, and one or more conductive powders.

83. (New) The method claim 62, wherein the voltage switchable dielectric material includes one or more polymer binders.

84. (New) The method claim 62, wherein the voltage switchable dielectric material includes one or more cross linking agents.